

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Trench MOSFET technology
- · Side wettable flanks for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 1 kV HBM (class H1C)
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V _{GS}	gate-source voltage	_		-8	-	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	8	А
Static chara	cteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 8 A; T _j = 25 °C		-	13	16	mΩ

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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5. Pinning information

Table 2.	Table 2. Pinning information							
Pin	Symbol	Description	Simplified outline	Graphic symbol				
1	D	drain		D				
2	D	drain						
3	G	gate		G ↓ ↓ ↓ ↓				
4	S	source	3 8 4					
5	D	drain	Transparent top view					
6	D	drain	DFN2020MD-6	s				
7	D	drain	(SOT1220)	017aaa255				
8	S	source						

6. Ordering information

Table 3. Ordering	information
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Type number			
	Name	Description	Version
PMPB13XNEA		DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220

7. Marking

Table 4. Marking codes					
Type number	Marking code				
PMPB13XNEA	4G				

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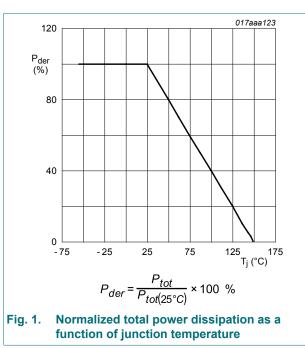
8. Limiting values

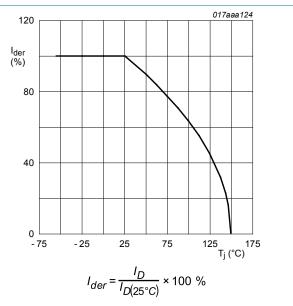
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	8	А
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	5	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	32	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.7	W
		T _{sp} = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode		•			
I _S	source current	T _{amb} = 25 °C	[1]	-	2	А
ESD maximu	um rating		•			
V _{ESD}	electrostatic discharge voltage	НВМ		-	1000	V
Avalanche r	uggedness	1				
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)} = 25 \text{ °C; } I_D = 1.35 \text{ A; DUT in}$ avalanche (unclamped)		-	21.3	mJ

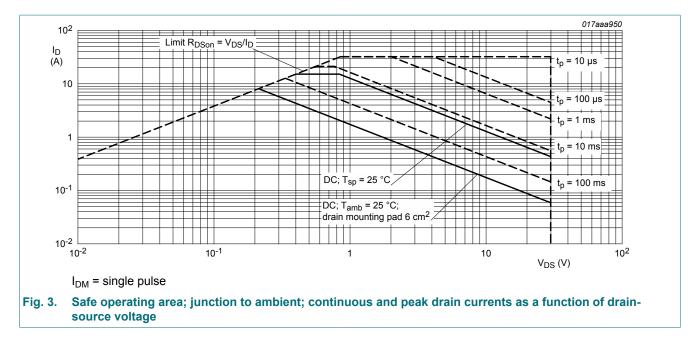
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².







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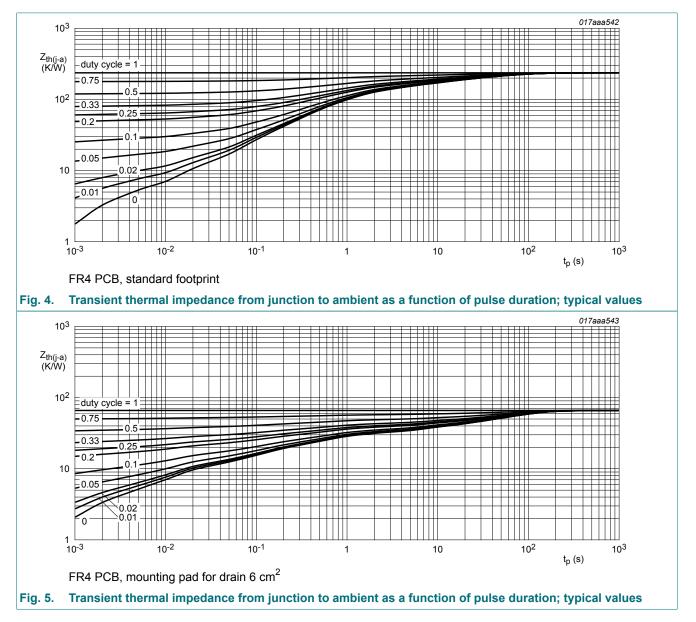


9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}			[1]	-	235	270	K/W
	junction to ambient		[2]	-	67	74	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	5	10	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

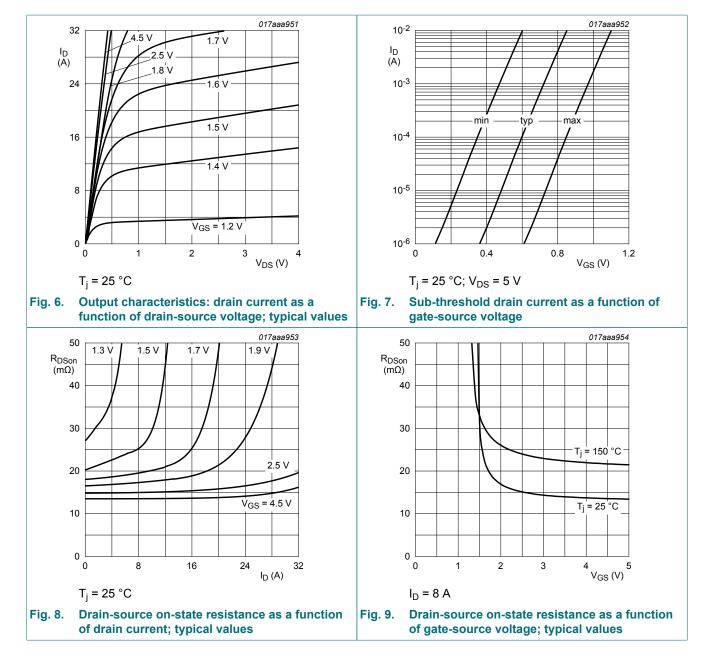
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = 250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	0.4	0.65	0.9	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 8 A; T _j = 25 °C	-	13	16	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 8 A; T _j = 150 °C	-	21	27	mΩ
		V _{GS} = 2.5 V; I _D = 7.2 A; T _j = 25 °C	-	14	20	mΩ
		V _{GS} = 1.8 V; I _D = 3.7 A; T _j = 25 °C	-	17	24	mΩ
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 8 A; T _j = 25 °C	-	60	-	S
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	-	2.1	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 6 A; V _{GS} = 4.5 V;	-	24	36	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	2.4	-	nC
Q _{GD}	gate-drain charge	1	-	4.6	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	2195	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	155	-	pF
C _{rss}	reverse transfer capacitance		-	135	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 6 A; V _{GS} = 4.5 V;	-	12	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	30	-	ns
t _{d(off)}	turn-off delay time	1	-	54	-	ns
t _f	fall time	1 – – – – – – – – – – – – – – – – – – –	-	49	-	ns
Source-drai	n diode	, , ,	I		-	
V _{SD}	source-drain voltage	I _S = 2 A; V _{GS} = 0 V; T _j = 25 °C	-	0.6	1.2	V
t _{rr}	reverse recovery time	I _S = 2 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	12	-	ns
Q _r	recovered charge	V _{DS} = 15 V; T _j = 25 °C	-	4	-	nC

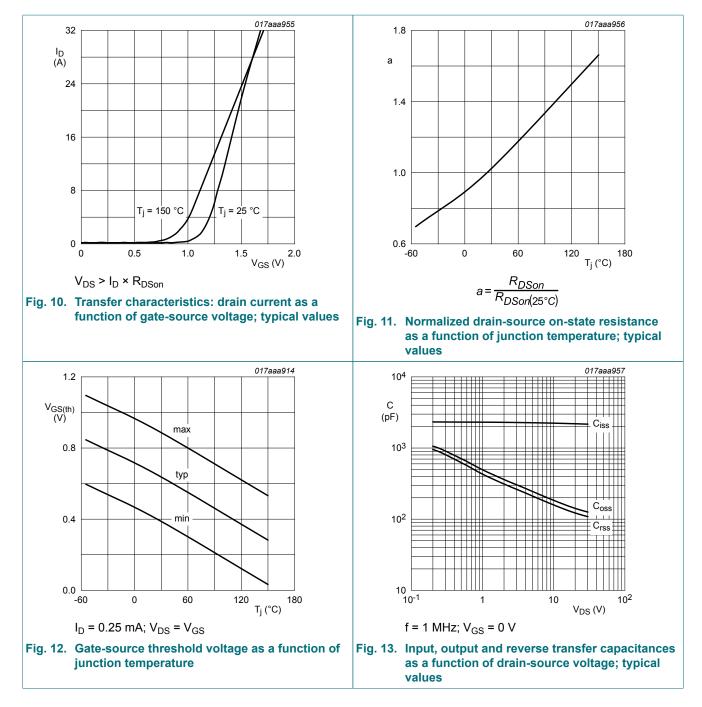
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Product data sheet

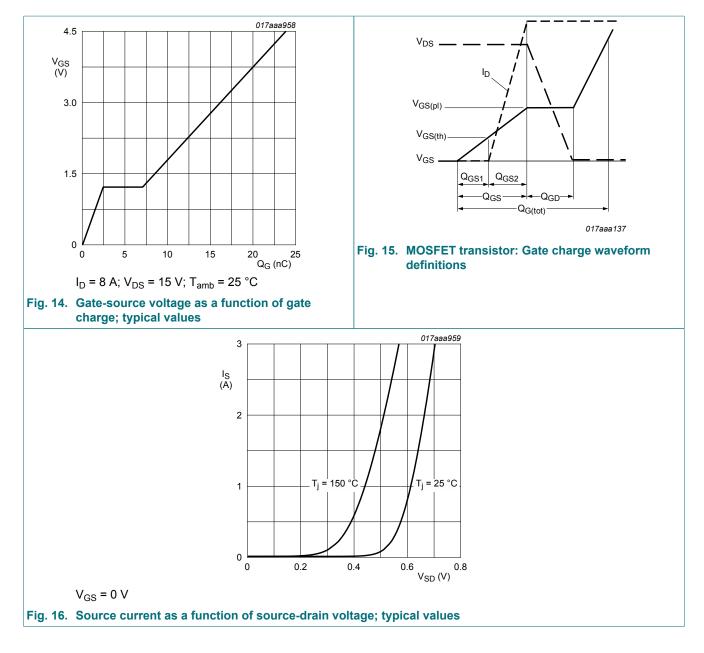
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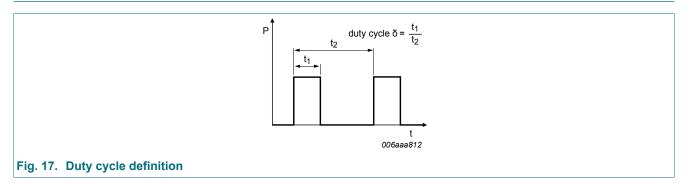


Product data sheet

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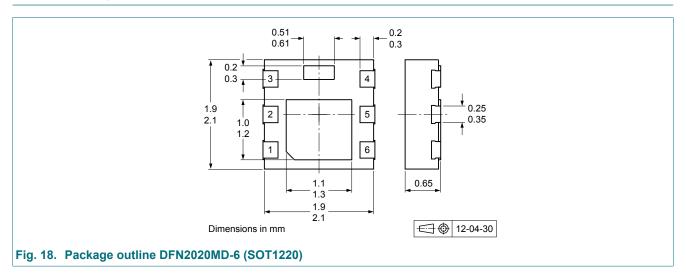
11. Test information



Quality information

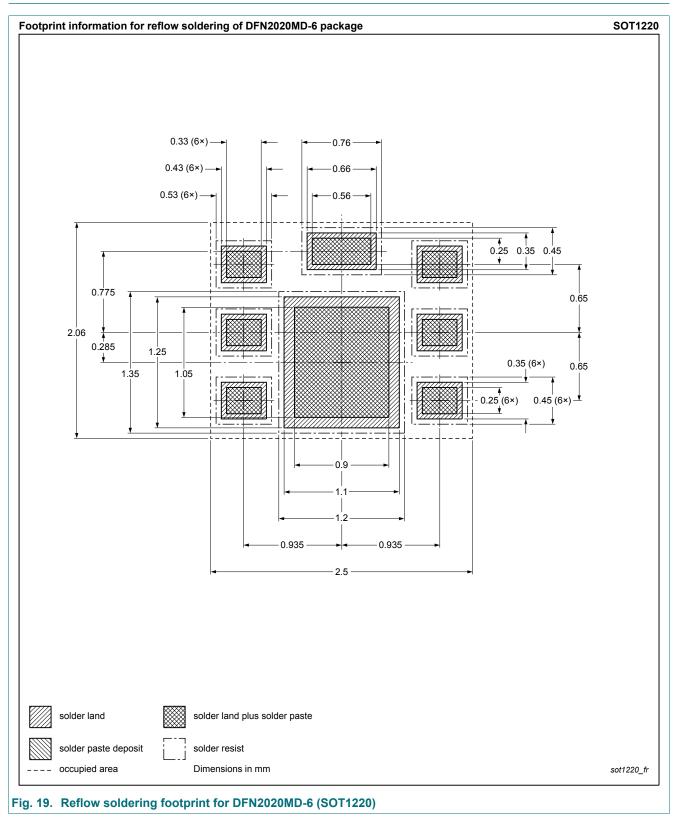
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMPB13XNEA v.1	20180910	Product data sheet	-	-		

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <u>https://www.nexperia.com</u>.

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